

### SEMIPACK<sup>®</sup> 3

### **Thyristor Modules**

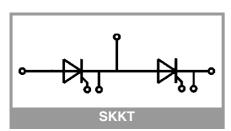
#### SKKT 280/22 E H4

#### Features\*

- Heat transfer through aluminum nitride ceramic insulated metal baseplate
- Precious metal pressure contacts for high reliability
- Thyristor with amplifying gate
- UL recognized, file no. E 63 532

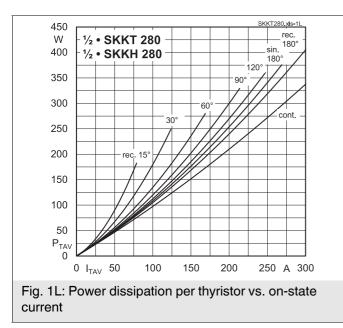
### Typical Applications

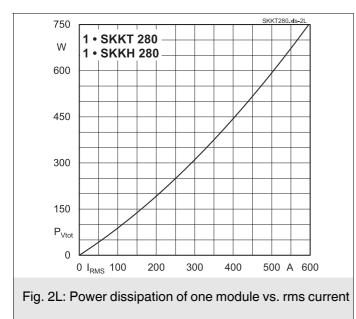
- DC motor control (e. g. for machine tools)
- AC motor starters
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)

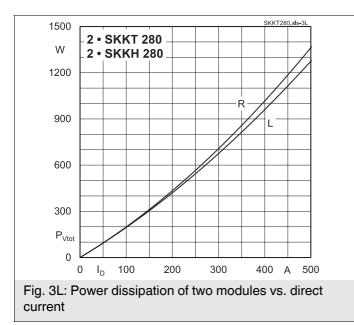


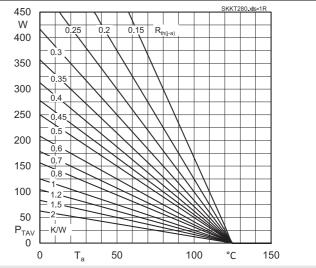
| Absolute              | Maximum Rating          | S                       |             |                  |
|-----------------------|-------------------------|-------------------------|-------------|------------------|
| Symbol                | Conditions              |                         | Values      | Unit             |
| Chip                  |                         |                         |             |                  |
| I <sub>T(AV)</sub>    | sinus 180°              | T <sub>c</sub> = 85 °C  | 252         | А                |
|                       |                         | T <sub>c</sub> = 79 °C  | 280         | A                |
| I <sub>TRMS</sub>     | continuous operation    |                         | 440         | A                |
| I <sub>TSM</sub>      | 10 ms                   | T <sub>j</sub> = 25 °C  | 8500        | А                |
|                       |                         | T <sub>j</sub> = 125 °C | 7500        | А                |
| i <sup>2</sup> t      | 10 ms                   | T <sub>j</sub> = 25 °C  | 361250      | A <sup>2</sup> s |
|                       |                         | T <sub>j</sub> = 125 °C | 281250      | A²s              |
| V <sub>RSM</sub>      |                         |                         | 2300        | V                |
| V <sub>RRM</sub>      |                         |                         | 2200        | V                |
| V <sub>DRM</sub>      |                         |                         | 2200        | V                |
| (di/dt) <sub>cr</sub> | T <sub>j</sub> = 125 °C |                         | 250         | A/µs             |
| (dv/dt) <sub>cr</sub> | T <sub>j</sub> = 125 °C |                         | 1000        | V/µs             |
| Tj                    |                         |                         | -40 125     | °C               |
| Module                |                         |                         |             |                  |
| T <sub>stg</sub>      |                         |                         | -40 125     | °C               |
| V <sub>isol</sub>     | a.c.; 50 Hz; r.m.s.     | 1 min                   | 4000        | V                |
|                       | a.c., 50 mz, 1.111.8.   | 1 s                     | 4800        | V                |
| Characte              | ristics                 |                         |             |                  |
| Symbol                | Conditions              |                         | min. typ. i | max. Unit        |

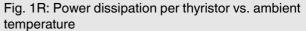
| Symbol                           | Conditions   |            | min. | typ. | max.     | Unit |
|----------------------------------|--|------------|------|------|----------|------|
| Chip                             |  |            |      |      |          |      |
| V <sub>T</sub>                   | T <sub>j</sub> = 25 °C, I <sub>T</sub> = 75                                  |            |      | 1.55 | V        |      |
| V <sub>T(TO)</sub>               | T <sub>i</sub> = 125 °C  |            |      |      | 0.90     | V    |
| r <sub>T</sub>                   | T <sub>j</sub> = 125 °C  |            |      |      | 0.75     | mΩ   |
| I <sub>DD</sub> ;I <sub>RD</sub> | $T_j = 125 \text{ °C}, V_{DD} = V_{DRM}; V_{RD} = V_{RRM}$                   |            |      |      | 90       | mA   |
| t <sub>gd</sub>                  | $T_j = 25 \text{ °C}, I_G = 1 \text{ A}, di_G/dt = 1 \text{ A}/\mu \text{s}$ |            |      | 1    |          | μs   |
| t <sub>gr</sub>                  | $V_{D} = 0.67 * V_{DRM}$   |            |      | 2    |          | μs   |
| t <sub>q</sub>                   | T <sub>j</sub> = 125 °C  |            | 50   | 150  | 150      | μs   |
| I <sub>H</sub>                   | $T_j = 25 \ ^{\circ}C$   |            |      | 150  | 500      | mA   |
| IL                               | $T_j = 25 \text{ °C}, R_G = 33 \Omega$                                       |            |      | 300  | 2000     | mA   |
| V <sub>GT</sub>                  | $T_j = 25 \ ^\circ C, \ d.c.$  |            | 3    |      |          | V    |
| I <sub>GT</sub>                  | $T_{j} = 25 \ ^{\circ}C, \ d.c.$   |            | 200  |      |          | mA   |
| $V_{\text{GD}}$                  | T <sub>j</sub> = 125 °C, d.c.  |            |      |      | 0.25     | V    |
| I <sub>GD</sub>                  | T <sub>j</sub> = 125 °C, d.c.  |            |      |      | 10       | mA   |
| $R_{\text{th(j-c)}}$             | continuous DC  | per chip   |      |      | 0.11     | K/W  |
|                                  |  | per module |      |      | 0.055    | K/W  |
| $R_{\text{th(j-c)}}$             | sin. 180°  | per chip   |      |      | 0.116    | K/W  |
|                                  |  | per module |      |      | 0.058    | K/W  |
| R <sub>th(j-c)</sub>             | - rec. 120°  | per chip   |      |      | 0.13     | K/W  |
|                                  |  | per module |      |      | 0.065    | K/W  |
| Module                           |  |            |      |      |          |      |
| R <sub>th(c-s)</sub>             | chip   |            |      | 0.04 |          | K/W  |
|                                  | module   |            |      | 0.02 |          | K/W  |
| Ms                               | to heatsink M5   |            | 4.25 |      | 5.75     | Nm   |
| Mt                               | to terminals M8  |            | 7.65 |      | 10.34    | Nm   |
| а                                |  |            |      |      | 5 * 9.81 | m/s² |
| W                                |  |            |      | 600  |          | g    |











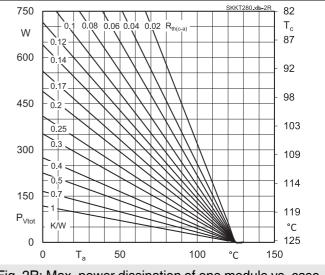
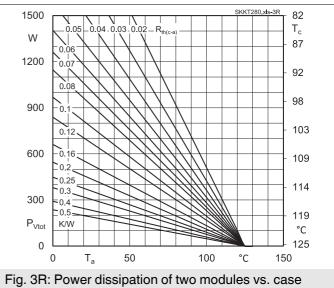
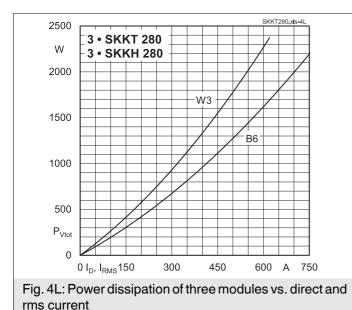
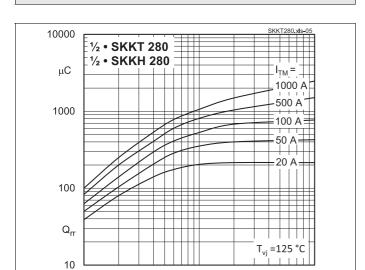


Fig. 2R: Max. power dissipation of one module vs. case temperature



temperature





10

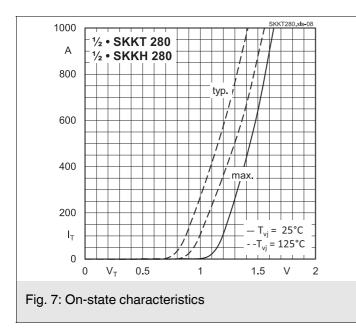
A/µs

100

Fig. 5: Recovered charge vs. current decrease

-di<sub>⊤</sub>/dt

1



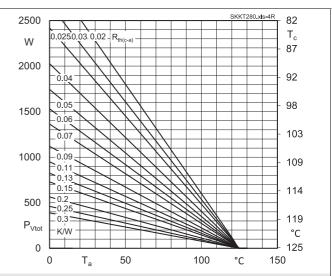


Fig. 4R: Power dissipation of three modules vs. case temperature

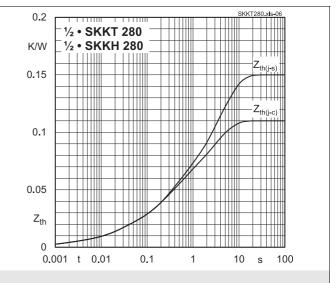
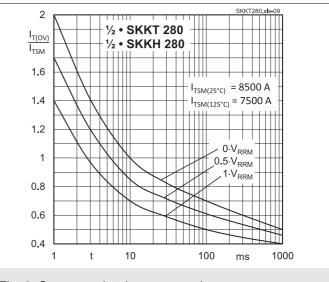
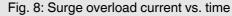
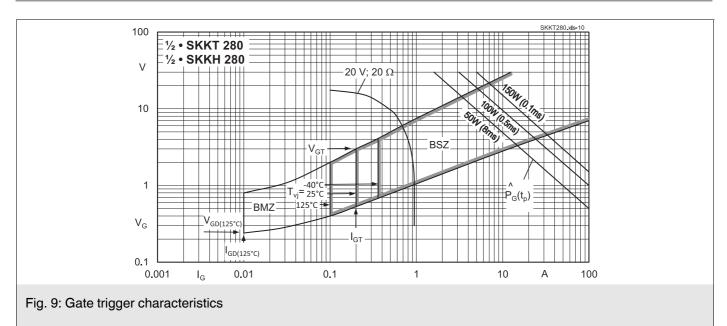
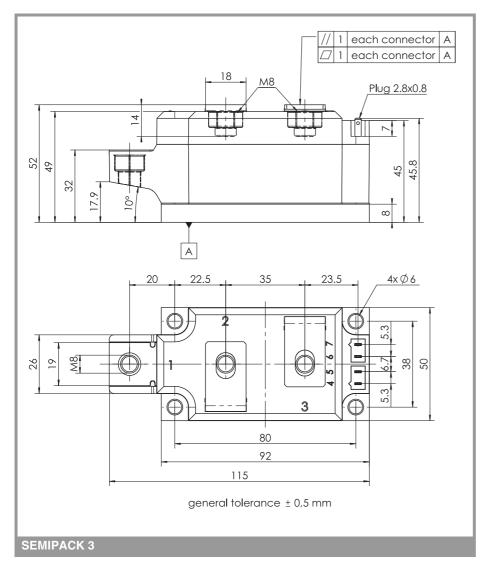


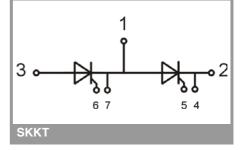
Fig. 6: Transient thermal impedance vs. time











This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

### \*IMPORTANT INFORMATION AND WARNINGS

The specifications of SEMIKRON products may not be considered as guarantee or assurance of product characteristics ("Beschaffenheitsgarantie"). The specifications of SEMIKRON products describe only the usual characteristics of products to be expected in

typical applications, which may still vary depending on the specific application. Therefore, products must be tested for the respective application in advance. Application adjustments may be necessary. The user of SEMIKRON products is responsible for the safety of their applications embedding SEMIKRON products and must take adequate safety measures to prevent the applications from causing a physical injury, fire or other problem if any of SEMIKRON products become faulty. The user is responsible to make sure that the application design is compliant with all applicable laws, regulations, norms and standards. Except as otherwise explicitly approved by SEMIKRON in a written document signed by authorized representatives of SEMIKRON, SEMIKRON products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury. No representation or warranty is given and no liability is assumed with respect to the accuracy, completeness and/or use of any information herein, including without limitation, warranties of non-infringement of intellectual property rights of any third party. SEMIKRON does not assume any liability arising out of the applications or use of any product; neither does it convey any license under its patent rights, copyrights, trade secrets or other intellectual property rights of any third party which may arise from applications. Due to technical requirements our products may contain dangerous substances. For information previously supplied and may be superseded by updates. SEMIKRON reserves the right to make changes.